Dual 2-input NAND gate

Rev. 1 — 21 March 2013

Product data sheet

1. General description

The 74AHC2G00-Q100; 74AHCT2G00-Q100 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Low power dissipation
- Balanced propagation delays
- Multiple package options

3. Ordering information

Table 1.Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AHC2G00DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads;	; SOT505-2				
74AHCT2G00DP-Q100			body width 3 mm; lead length 0.5 mm					
74AHC2G00DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package;	SOT765-1				
74AHCT2G00DC-Q100			8 leads; body width 2.3 mm					



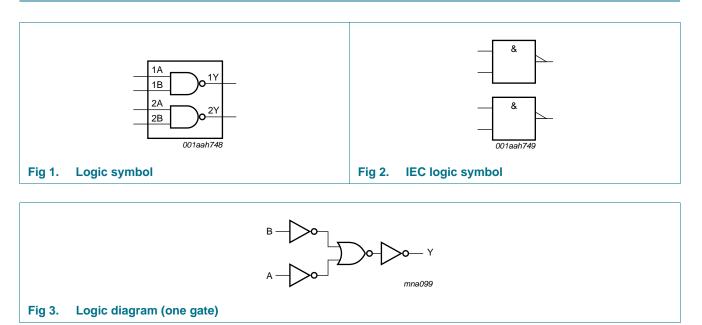
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4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AHC2G00DP-Q100	A00
74AHCT2G00DP-Q100	C00
74AHC2G00DC-Q100	A00
74AHCT2G00DC-Q100	C00

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

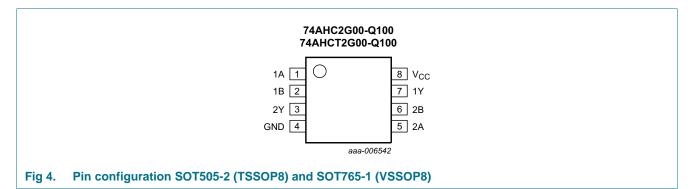
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input	Output	
nA	nB	nY
L	L	Н
L	н	Н
Н	L	Н
Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	V _I < -0.5 V	<u>[1]</u> –20	-	mA
Ι _{ΟΚ}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	75	mA
I _{GND}	ground current		-75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	arameter Conditions			Q100	74AH	Unit		
			Min	Тур	Max	Min	Тур	Max	_
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	∆t/∆V input transition rise and fall rate	V_{CC} = 3.3 V \pm 0.3 V	-	-	100	-	-	-	ns/V
		V_{CC} = 5.0 V \pm 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol Parameter		Conditions		25 °C		–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Тур	Мах	Min	Max	Min	Max	
74AHC2	G00-Q100									
V _{IH}	HIGH-level input voltage	$V_{CC} = 2.0 V$	1.5	-	-	1.5	-	1.5	-	V
		$V_{CC} = 3.0 V$	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 5.5 V$	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	-	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 3.0 V$	-	-	0.9	-	0.9	-	0.9	V
		$V_{CC} = 5.5 V$	-	-	1.65	-	1.65	-	1.65	V

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Symbol	Parameter	Conditions		25 °C		–40 °C	to +85 °C	–40 °C to +125 °C		Uni
			Min	Тур	Max	Min	Max	Min	Max	
V _{ОН}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	I_{O} = –50 $\mu\text{A};V_{CC}$ = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = –50 $\mu\text{A};V_{CC}$ = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V
		I_{O} = -50 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V
		I_{O} = -8.0 mA; V_{CC} = 4.5 V	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_I = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		$I_0 = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current		-	-	10	-	10	-	40	μA
CI	input capacitance		-	1.5	10	-	10	-	10	pF
74АНСТ	2G00-Q100									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -8.0 mA	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		l _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	supply current	$V_1 = V_{CC}$ or GND; $I_0 = 0$ A; $V_{CC} = 5.5$ V	-	-	1.0	-	10	-	40	μA
∕l ^{CC}	additional supply current	per input pin; $V_I = 3.4 V$; other inputs at V_{CC} or GND; $I_O = 0 A$; $V_{CC} = 5.5 V$	-	-	1.35	-	1.5	-	1.5	m/
Cı	input capacitance		-	1.5	10	-	10	-	10	pF

Table 7.Static characteristics ... continuedVoltages are referenced to GND (ground = 0 V).

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11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; for test circuit see <u>Figure 6</u>.

Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74AHC2	G00-Q100										
t _{pd}	propagation	nA, nB to nY; see Figure 5	[1]								
	delay	V_{CC} = 3.0 V to 3.6 V	[2]								
		C _L = 15 pF		-	4.5	7.9	1.0	9.5	1.0	10.5	ns
		C _L = 50 pF		-	6.5	11.4	1.0	13.0	1.0	14.5	ns
		V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		-	3.5	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF		-	4.9	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	per buffer; $C_L = 50 \text{ pF}; f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	<u>[4]</u>	-	17	-	-	-	-	-	pF
74AHCT	2G00-Q100										
t _{pd}	propagation	nA, nB to nY; see Figure 5	[1]								
	delay	V_{CC} = 4.5 V to 5.5 V	[3]								
		C _L = 15 pF		1.0	3.6	6.2	1.0	7.1	1.0	8.0	ns
		C _L = 50 pF		1.0	5.0	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	per buffer; C _L = 50 pF; f _i = 1 MHz; V _I = GND to V _{CC}	<u>[4]</u>	-	18	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] Typical values are measured at V_{CC} = 3.3 V.

[3] Typical values are measured at $V_{CC} = 5.0$ V.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where: f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

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12. Waveforms

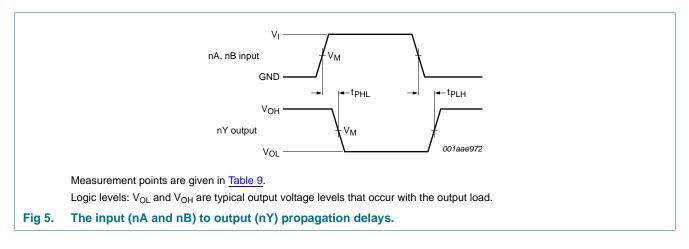


Table 9.Measurement points

Туре	Input	Output
	V _M	V _M
74AHC2G00-Q100	0.5V _{CC}	0.5V _{CC}
74AHCT2G00-Q100	1.5 V	0.5V _{CC}

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74AHC2G00-Q100; 74AHCT2G00-Q100

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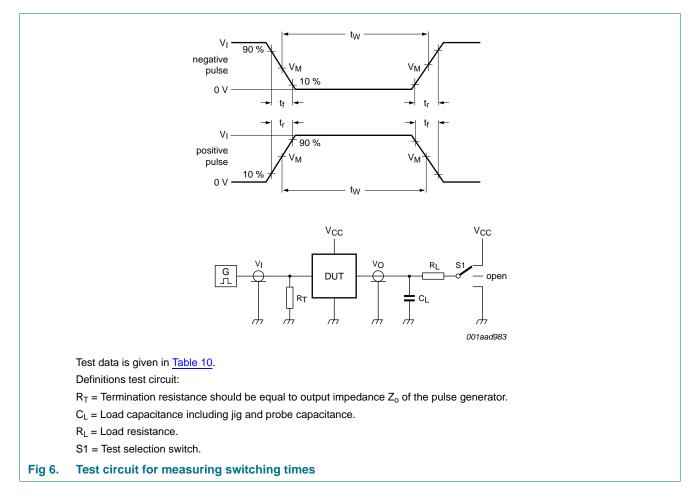


Table 10.Test data

Туре	Input		Load	S1 position	
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74AHC2G00-Q100	V _{CC}	≤ 3 ns	15 pF, 50 pF	1 kΩ	open
74AHCT2G00-Q100	3 V	\leq 3 ns	15 pF, 50 pF	1 kΩ	open

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13. Package outline

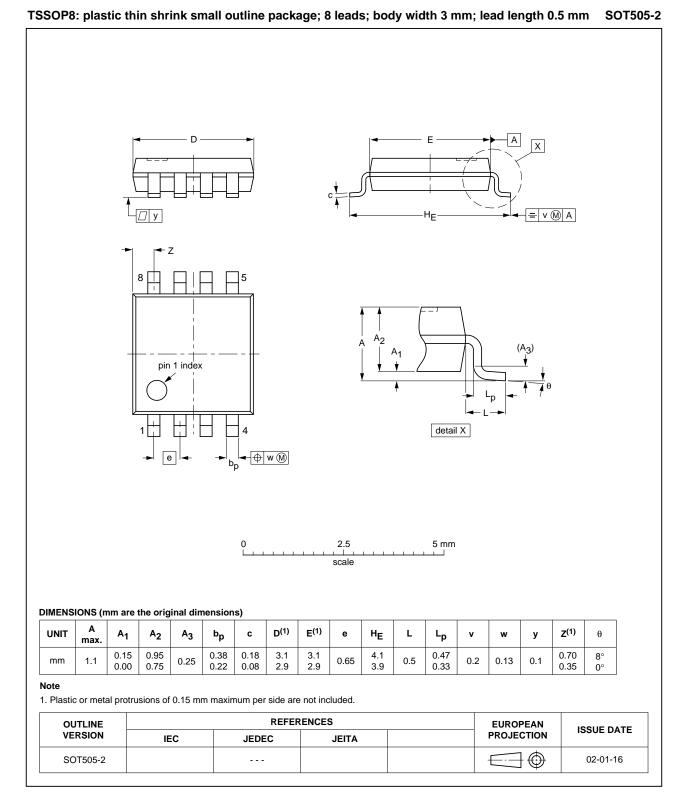


Fig 7. Package outline SOT505-2 (TSSOP8)

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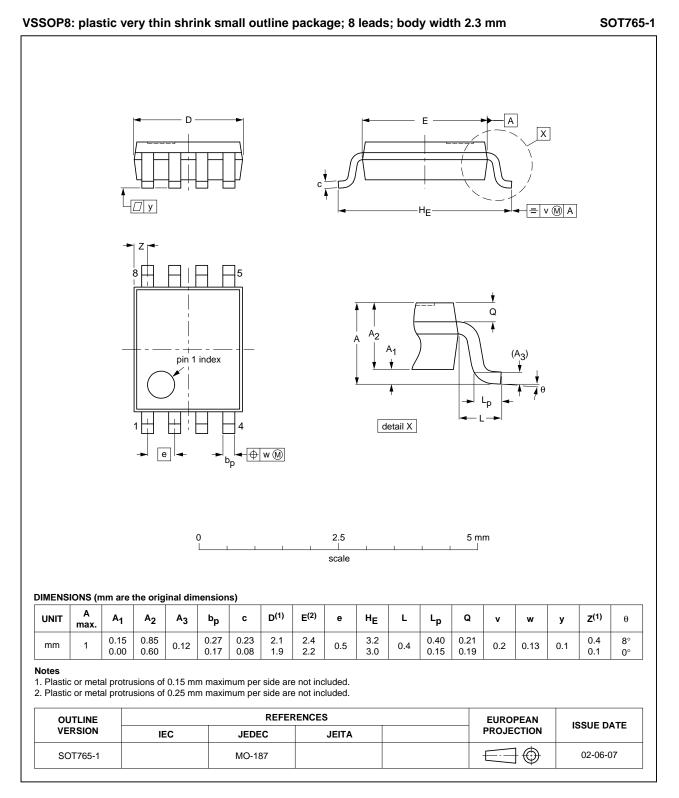


Fig 8. Package outline SOT765-1 (VSSOP8)

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14. Abbreviations

Description
Charged Device Model
Complementary Metal-Oxide Semiconductor
Device Under Test
ElectroStatic Discharge
Human Body Model
Machine Model
Transistor-Transistor Logic
Military

15. Revision history

Table 12. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT2G00_Q100 v.1	20130321	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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